Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Trench MOSFET technology

3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	6.9	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 5.1 A; T_j = 25 °C		-	30	43	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain		
3	G	gate	2 5	G G 大 大
4	S	source	3 8 94	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S
7	D	drain		017aaa255
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB50ENE	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB50ENE	3U

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	6.9	А
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	5.1	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	3.2	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	20	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.9	mW
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{sp} = 25 °C		-	11	W
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain di	ode		•			
I _S	source current	T _{amb} = 25 °C	[1]	-	2	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

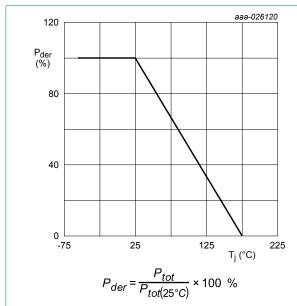


Fig. 1. Normalized total power dissipation as a function of junction temperature

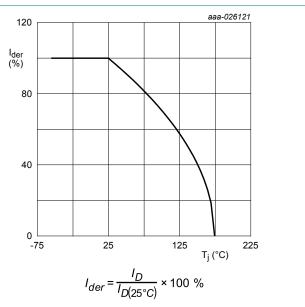


Fig. 2. Normalized continuous drain current as a function of junction temperature

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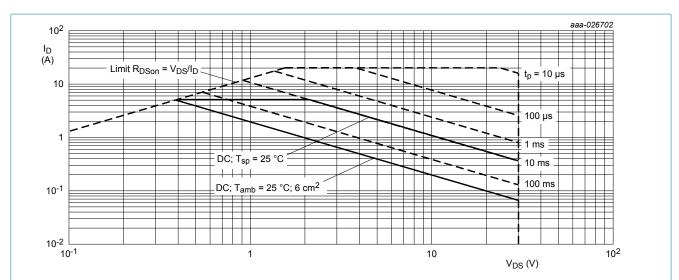


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	238	274	K/W
			[2]	-	67	77	K/W
		in free air; t ≤ 5 s	[2]	-	35	40	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	11	14	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

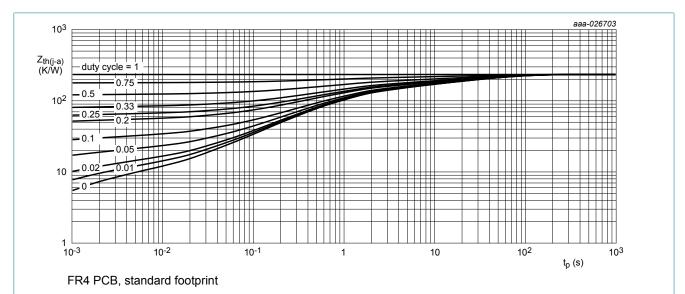


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

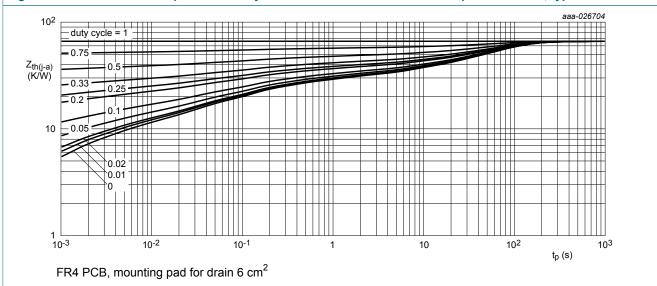


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C	1	1.5	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	200	nA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-200	nA
D3011	drain-source on-state	V _{GS} = 10 V; I _D = 5.1 A; T _j = 25 °C	-	30	43	mΩ
	resistance	V _{GS} = 10 V; I _D = 5.1 A; T _j = 175 °C	-	54	78	mΩ
		V _{GS} = 4.5 V; I _D = 4.2 A; T _j = 25 °C	-	39	60	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 5.1 A; T_j = 25 °C	-	13	-	S
R _G	gate resistance	f = 1 MHz	-	6.6	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 5.1 A; V _{GS} = 10 V;	-	6	10	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	1.3	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	271	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	58	-	pF
C _{rss}	reverse transfer capacitance		-	43	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5.1 A; V _{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t _{d(off)}	turn-off delay time	_	-	17	-	ns
t _f	fall time	_	-	6	-	ns
Source-dra	in diode		'			
V_{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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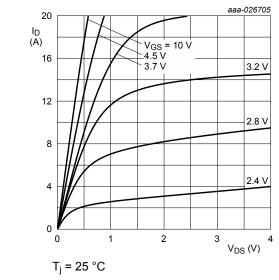


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

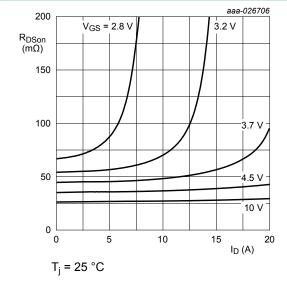


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

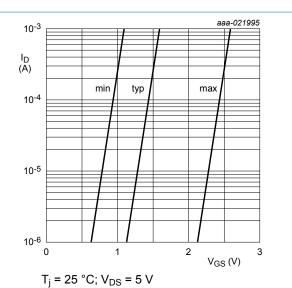


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

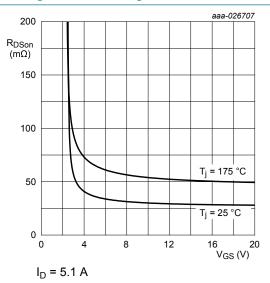


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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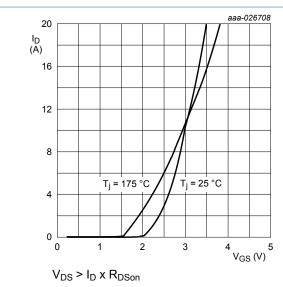


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

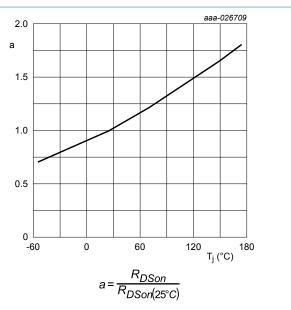


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

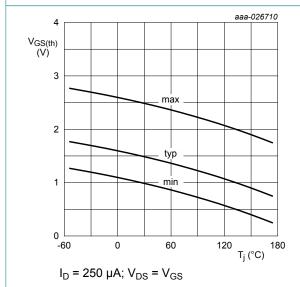


Fig. 12. Gate-source threshold voltage as a function of junction temperature

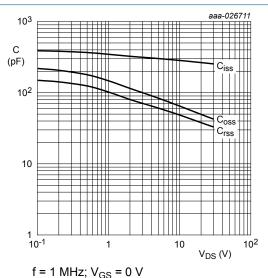


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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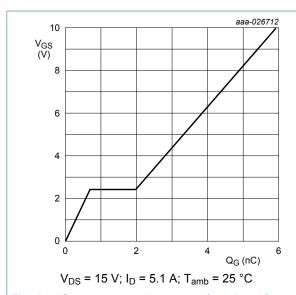


Fig. 14. Gate-source voltage as a function of gate charge; typical values

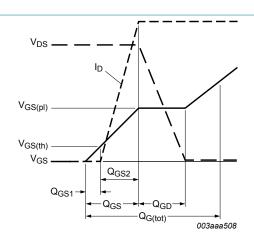


Fig. 15. Gate charge waveform definitions

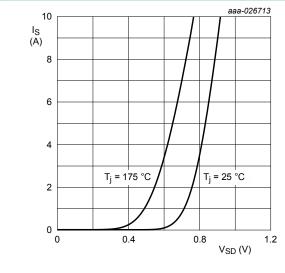
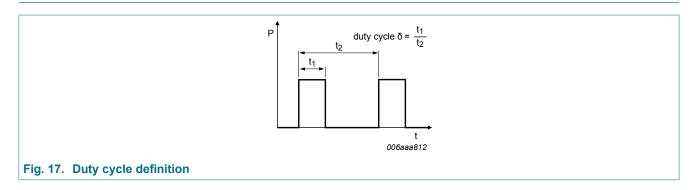


Fig. 16. Source current as a function of source-drain voltage; typical values

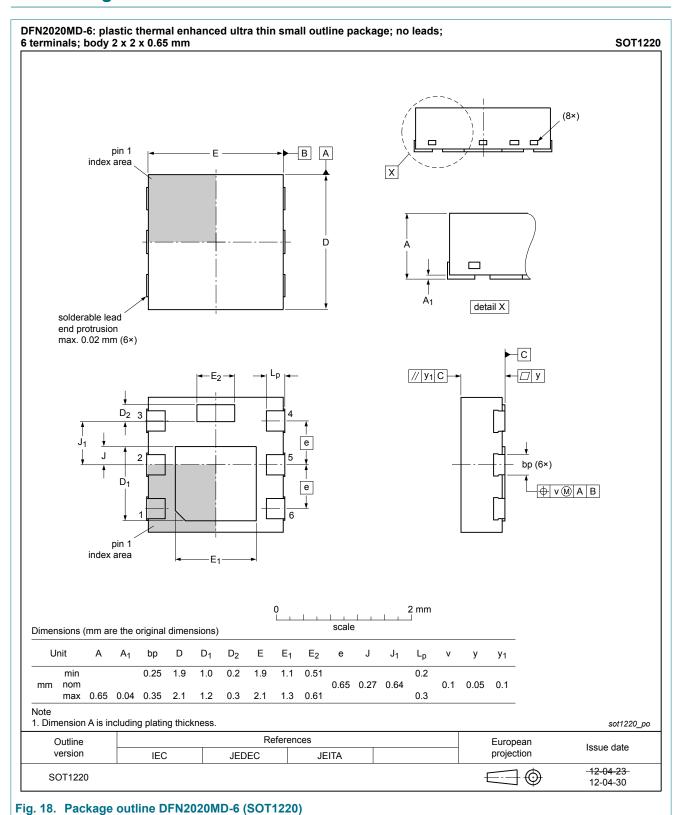
11. Test information

 $V_{GS} = 0 V$



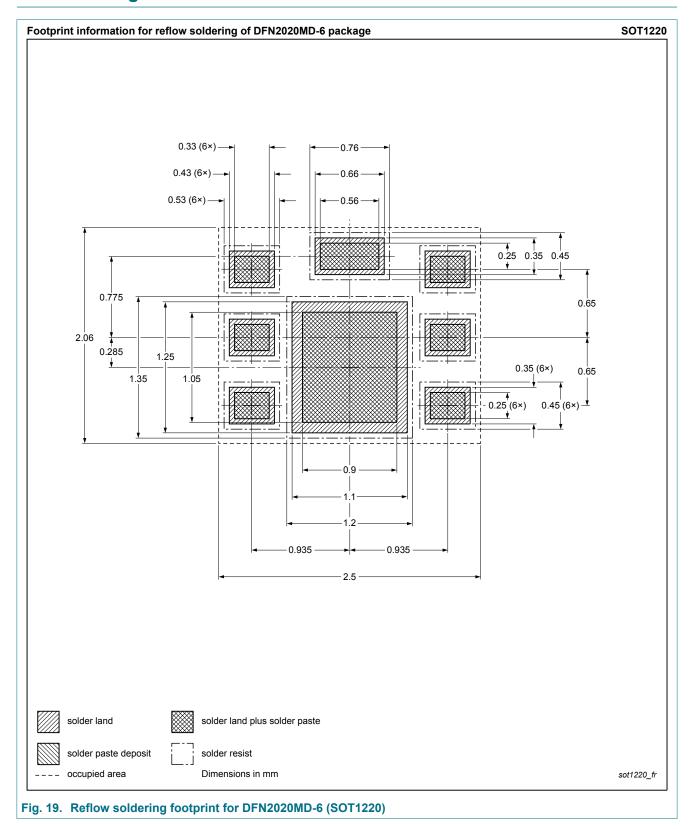
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB50ENE v.1	20180426	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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